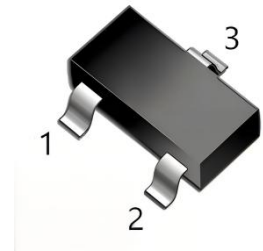


TRANSISTOR (NPN)

Parameter	Value	Unit
V_{CEO}	25	V
I_C	1.5	A

1. BASE
2. EMITTER
3. COLLECTOR



SOT-23

Features

- Complementary to PNP Transistor SS8550
- Power dissipation of 300mW
- High stability and high reliability

Absolute Maximum Ratings (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	1.5	A
P_C	Total Device Dissipation	300	mW
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	-55 ~ +150	°C
$R_{\theta JA}$	Thermal Resistance From Junction to Ambient	417	°C/W

Note:

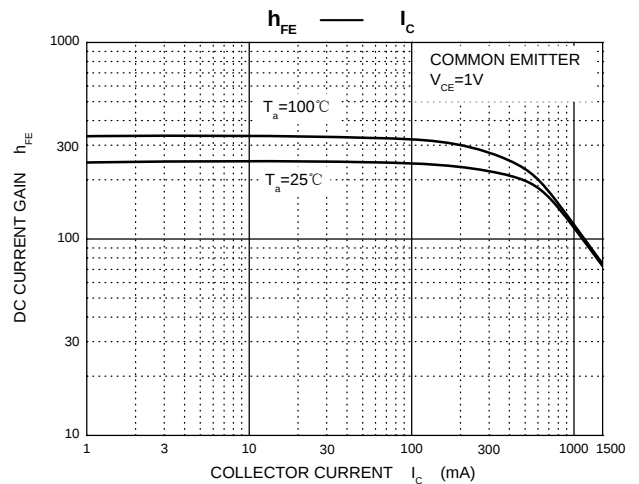
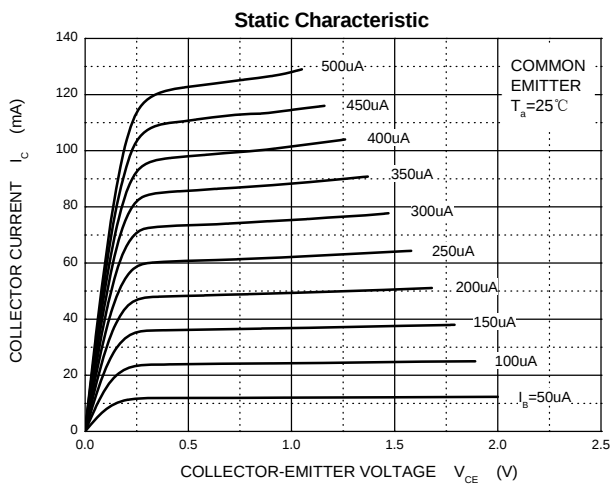
Absolute maximum ratings are those values beyond which the device could be permanently damaged.

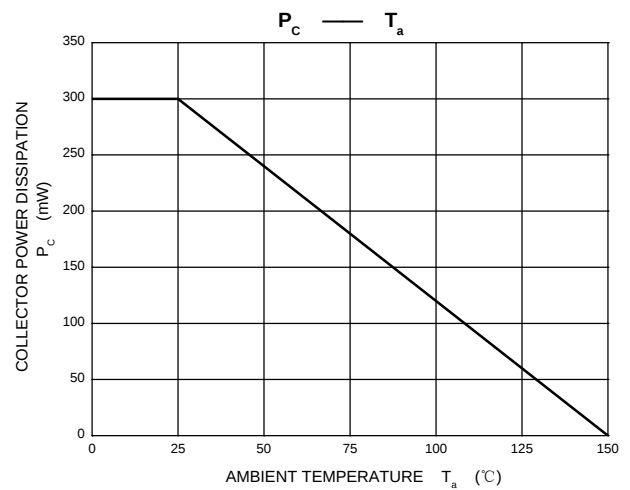
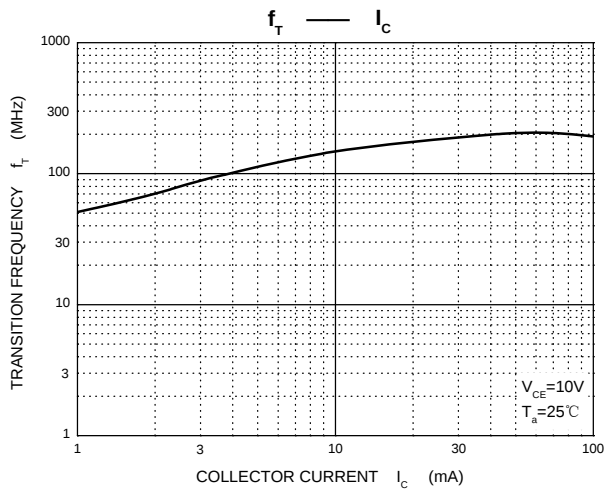
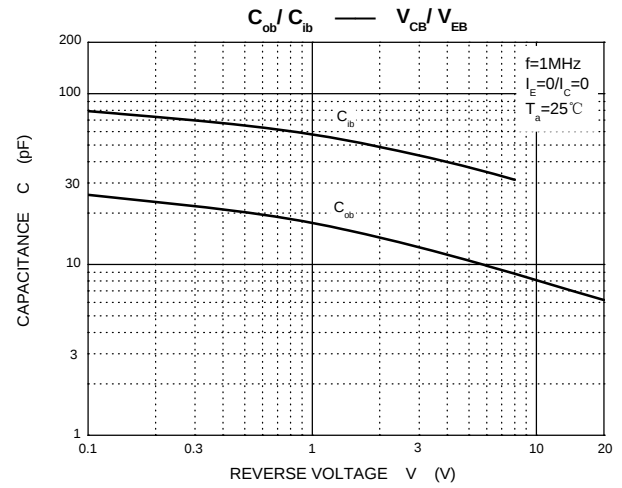
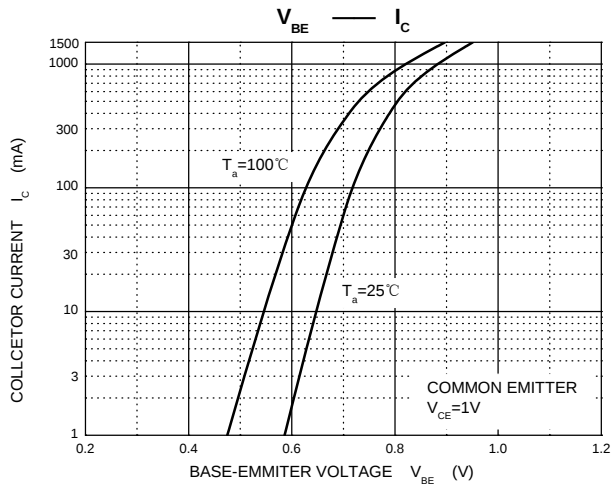
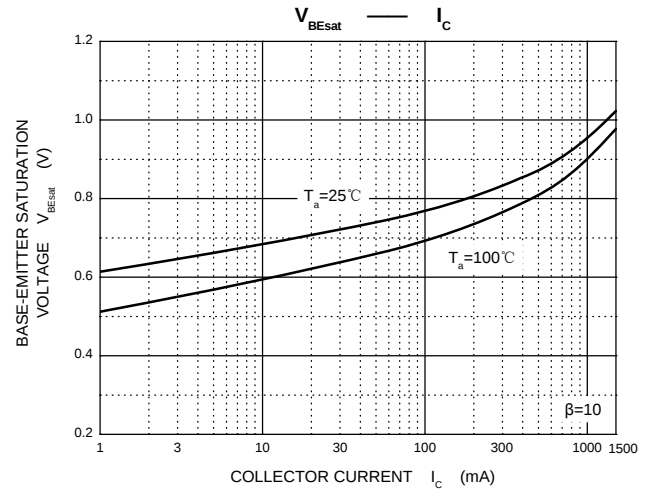
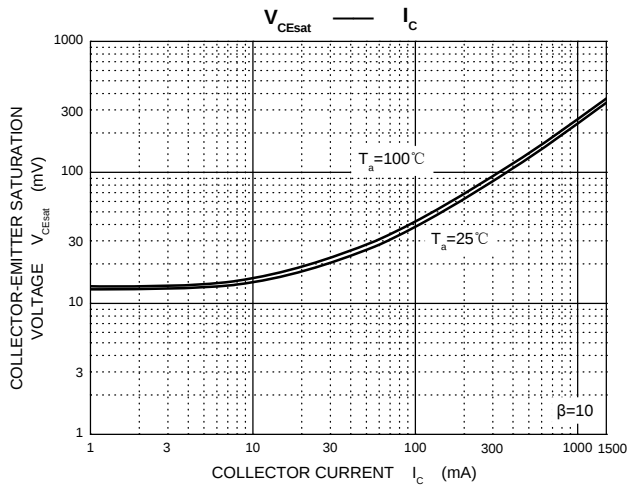
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

Electrical Characteristics(Ta=25°C unless otherwise noted)

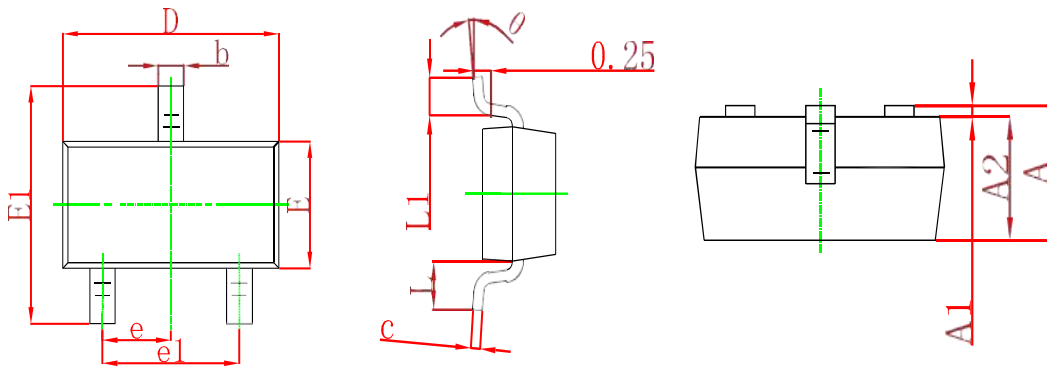
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=0.1mA, I_B=0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cutoff current	I_{CBO}	$V_{CB}=40V, I_E=0$			0.1	μA
Collector cutoff current	I_{CEO}	$V_{CE}=20V, I_E=0$			0.1	μA
Emitter cutoff current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.1	μA
DC Current Gain (CLASSIFICATION OF h_{FE1})	h_{FE1}	$V_{CE}=1V, I_C=100mA$	120		200	
			200		350	
			300		400	
	h_{FE2}	$V_{CE}=1V, I_C=800mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=800mA, I_B=80mA$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=800mA, I_B=80mA$			1.2	V
Transition frequency	f_T	$V_{CE}=10V, I_C=50mA, f=30MHz$	100			MHz

Typical Characteristics





Package Outline Dimensions
SOT-23



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

***Important Usage Information and Disclaimer**

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